

isc N-Channel MOSFET Transistor

2SK319

DESCRIPTION

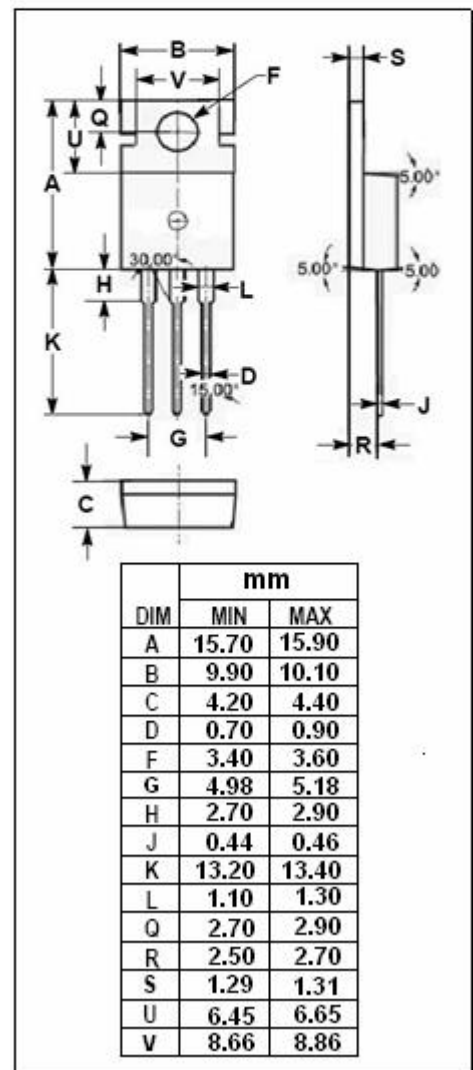
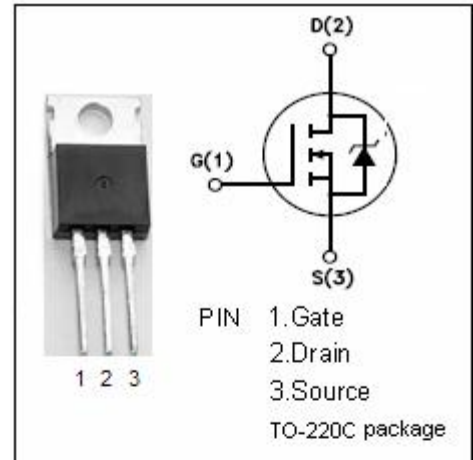
- Drain Current $-I_D=5A @ T_C=25^\circ C$
- Drain Source Voltage-
: $V_{DSS}= 400V(\text{Min})$
- Fast Switching Speed

APPLICATIONS

- High speed power Switching.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	400	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $T_C=25^\circ C$	5	A
P_{tot}	Total Dissipation@ $T_C=25^\circ C$	50	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



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• ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=10\text{mA}$	400			V
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=10V_{GS}; I_D=1\text{mA}$	1.0		5.0	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	$V_{GS}=15\text{V}; I_D=3\text{A}$		1.10	1.83	Ω
I_{GSS}	Gate Source Leakage Current	$V_{GS}=\pm 20\text{V}; V_{DS}=0$			± 1	μA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=320\text{V}; V_{GS}=0$			1	mA
V_{SD}	Diode Forward Voltage	$I_F=3\text{A}; V_{GS}=0$		0.85		V
t_r	Rise time	$V_{GS}=15\text{V}; I_D=2\text{A}; R_L=15\Omega$		35		ns
t_{on}	Turn-on time			50		ns
t_f	Fall time			35		ns
t_{off}	Turn-off time			120		ns